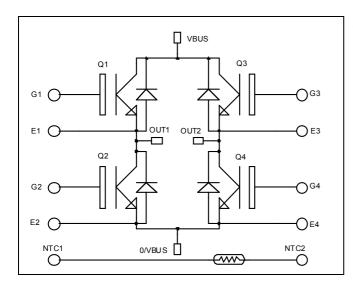


Full - Bridge Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 600V$$

 $I_{C} = 150A$ @ $Tc = 80$ °C



Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



O/VBUS OUT1 **VBUS** E2 🛭 NTC2 NTC1 (0

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	225	
$I_{\rm C}$	Continuous Collector Current	$T_C = 80$ °C	150	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	350	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	480	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	300A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.5	1.9	V
$V_{CE(sat)}$	Confector Emitter Saturation Voltage	$I_C = 150A$ $T_j =$	$T_j = 150$ °C		1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		9200		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		580		pF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		270		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		115		
T_{r}	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 150A$		225		ns
$T_{\rm f}$	Fall Time	$R_G = 3.3\Omega$		55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C	O \	130		
T_{r}	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 150A$ $R_{G} = 3.3\Omega$		50		ns
$T_{d(off)}$	Turn-off Delay Time			300		113
$T_{\rm f}$	Fall Time			70		
Е	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.85		mJ
Eon	$V_{\text{Bus}} = 300\text{V}$	$V_{\text{Bus}} = 300 \text{V}$ $T_{\text{j}} = 150 ^{\circ} \text{C}$		1.5		1117
Е	Turn off Energy	$I_C = 150A$ $T_j = 25^{\circ}C$ $T_j = 150^{\circ}C$		4.1		m I
E_{off}				5.3		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R=600V$	$T_j = 25^{\circ}C$			250	μA
I_{F}	DC Forward Current		$T_{i} = 150^{\circ}C$ $Tc = 80^{\circ}C$		150	500	A
V	Diode Forward Voltage	$I_F = 150A$ $V_{GE} = 0V$	$T_j = 25^{\circ}C$		1.6	2	V
V_{F}	Diode Polward Voltage		$T_{i} = 150^{\circ}C$		1.5		·
t	t _{rr} Reverse Recovery Time		$T_j = 25^{\circ}C$		130		ns
٩rr		$T_j = 150$ °C		225		113	
0	Q_{rr} Reverse Recovery Charge $V_R = 300V_R$	$I_F = 150A$	$T_j = 25^{\circ}C$		6.9		μC
Qrr		$di/dt = 3000 A/\mu s$	$T_{i} = 150^{\circ}C$		14.5		μС
E _r	Reverse Recovery Energy	<u> </u>	$T_j = 25^{\circ}C$		1.6		mJ
			$T_{\rm j} = 150^{\circ}{\rm C}$		3.5		1113



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

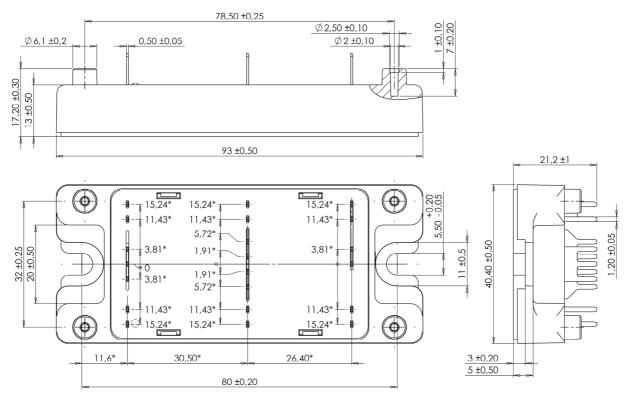
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.31	°C/W
TthJC			Diode			0.52	C/ W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)



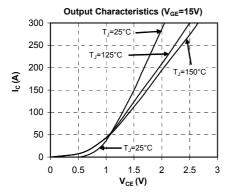
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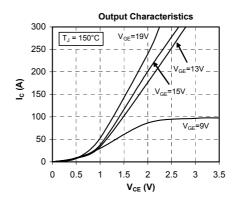
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

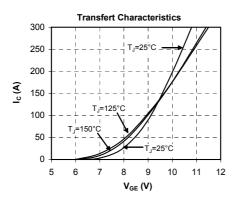
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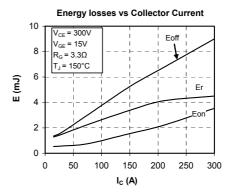


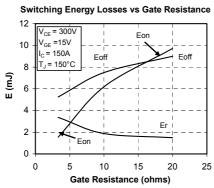
Typical Performance Curve

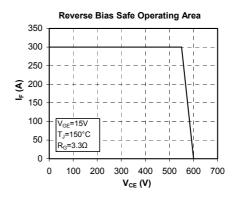


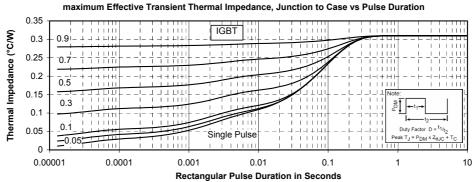




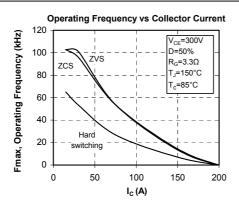


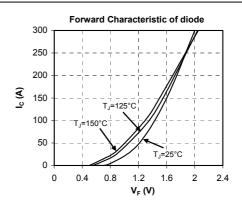


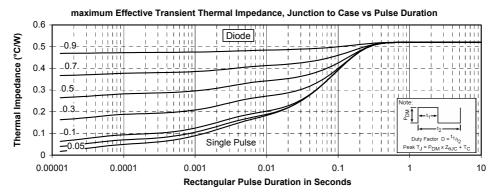












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